Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	40	V	
V _{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	4.8	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 4.8 \text{ A}; T_j = 25 \text{ °C}$		-	23	30	mΩ	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV30ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV30ENEA	R6%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	40	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	4.8	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	3.4	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	19	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	710	mW
			[1]	-	1.3	W
		T _{sp} = 25 °C		-	8.3	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drain o	liode				•	
Is	source current	T _{amb} = 25 °C	[1]	-	1.3	А
ESD maximum	rating				•	
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Avalanche rug	gedness		-	1	,	,
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = 0.83 A; DUT in avalanche (unclamped)		-	16.7	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 2 .
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

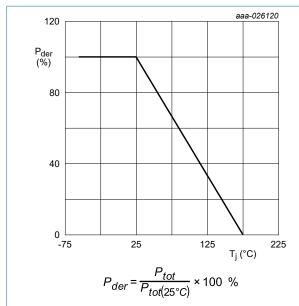
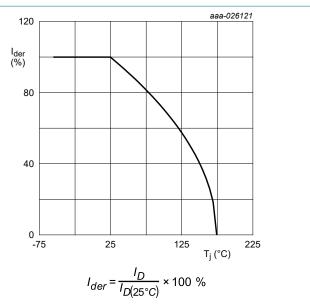


Fig. 1. Normalized total power dissipation as a function of junction temperature



ig. 2. Normalized continuous drain current as a function of junction temperature

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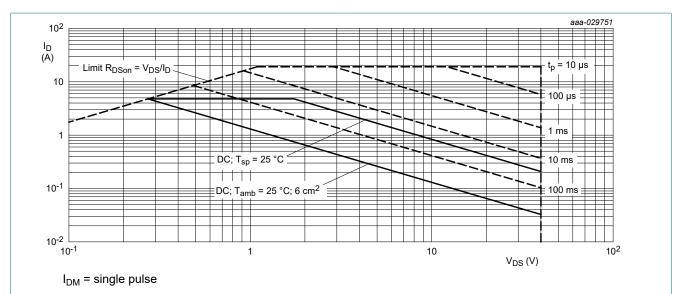


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

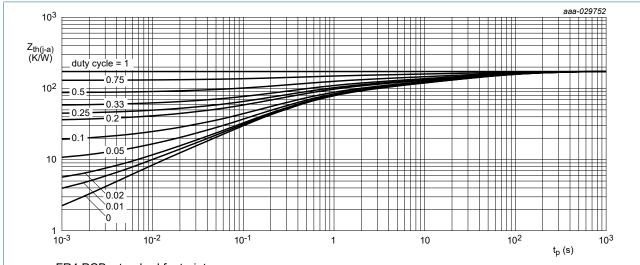
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9. Thermal characteristics

Table 6. Thermal characteristics

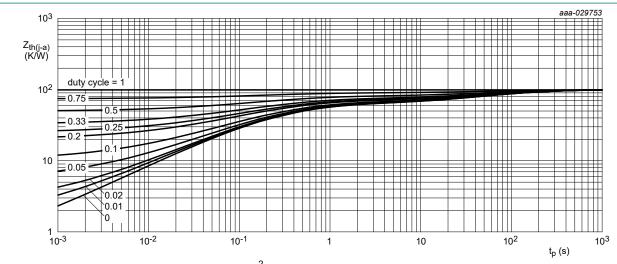
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	175	210	K/W
junction to ambient		[2]	-	95	115	K/W	
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.6	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 4.8 A; T _j = 25 °C	-	23	30	mΩ
resistance	resistance	V _{GS} = 10 V; I _D = 4.8 A; T _j = 175 °C	-	44	57	mΩ
		V _{GS} = 4.5 V; I _D = 4.1 A; T _j = 25 °C	-	30	40	mΩ
9fs	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$	-	19	-	S
R_{G}	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	naracteristics				'	
Q _{G(tot)}	total gate charge	V _{DS} = 20 V; I _D = 4.8 A; V _{GS} = 10 V;	-	7.8	11.7	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	1.2	-	nC
Q_{GD}	gate-drain charge		-	1.6	-	nC
C _{iss}	input capacitance	V _{DS} = 20 V; f = 1 MHz; V _{GS} = 0 V;	-	440	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	76	-	pF
C _{rss}	reverse transfer capacitance		-	39	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 20 V; I _D = 4.8 A; V _{GS} = 10 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	2	-	ns
t _{d(off)}	turn-off delay time		-	20	-	ns
t _f	fall time	1	-	33	-	ns
Source-dra	in diode		'	,		
V _{SD}	source-drain voltage	I _S = 1.3 A; V _{GS} = 0 V; T _j = 25 °C	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 1.3 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	11	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	4	-	nC

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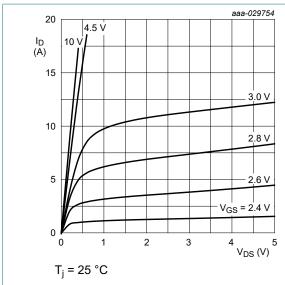


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

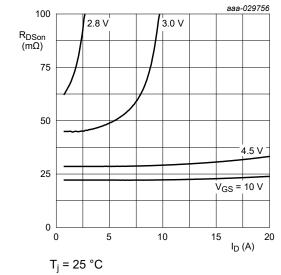


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

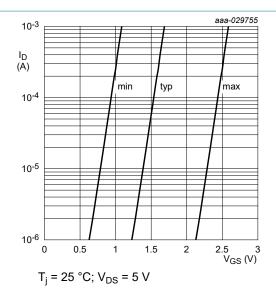


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

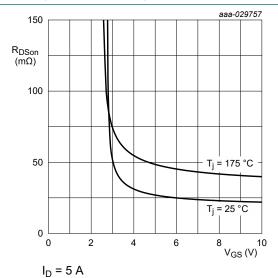


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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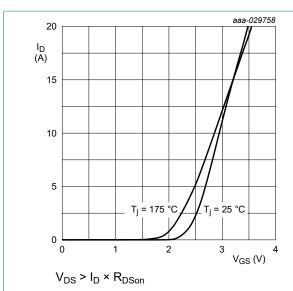


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

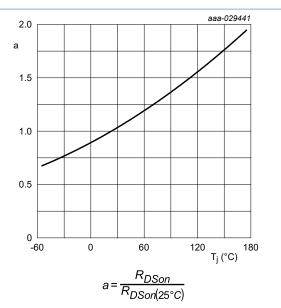


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

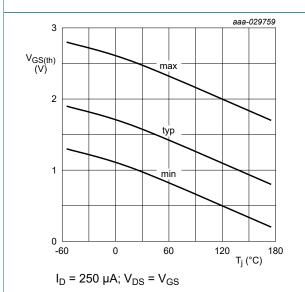


Fig. 12. Gate-source threshold voltage as a function of junction temperature

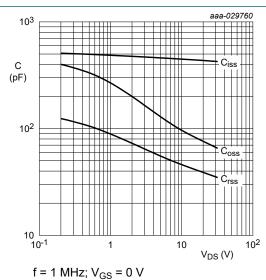


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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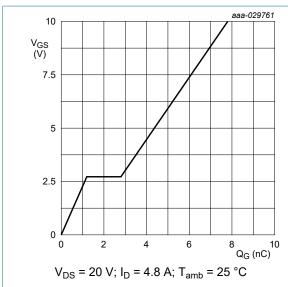


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

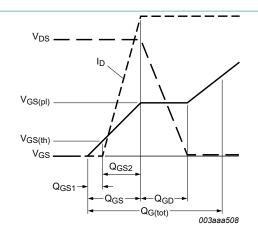


Fig. 15. Gate charge waveform definitions

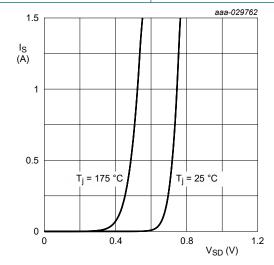
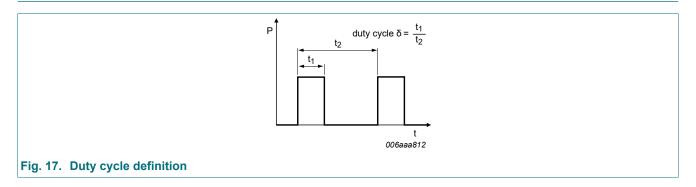


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

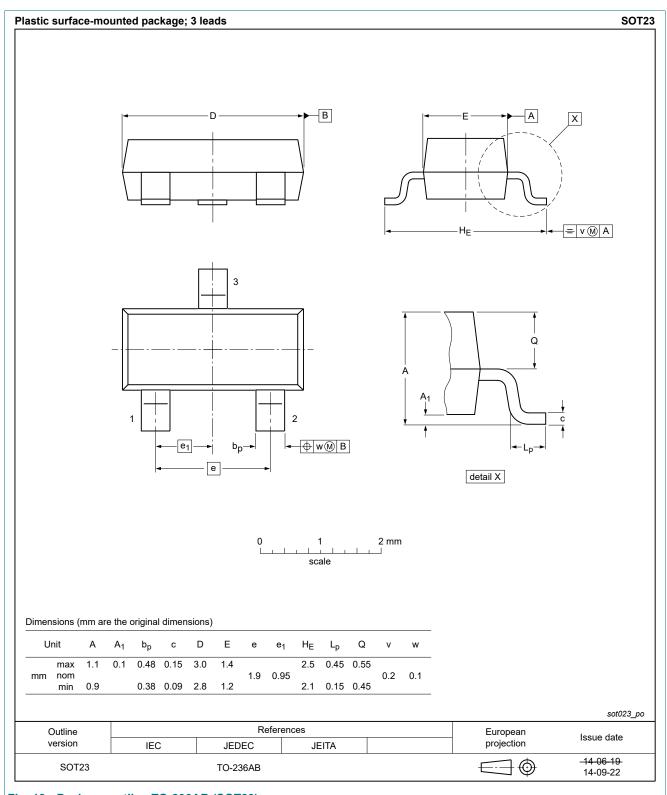


Fig. 18. Package outline TO-236AB (SOT23)

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13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV30ENEA v.1	20190402	Product data sheet	-	-

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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